IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Priority Application Serial No.	10/330,881
Priority Filing Date	December 23, 2002
Inventor	Trung Tri Doan et al.
Assignee	Micron Technology, Inc.
Priority Group Art Unit	2813
Priority Examiner	David S. Blum
Attorney Docket No.	MI22-2416
Customer No.	021567
Title	Methods of Forming Trench Isolation Regions

INFORMATION DISCLOSURE STATEMENT PURSUANT TO 37 C.F.R. §§ 1.56, 1.97 AND 1.98

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a divisional application of co-pending application Serial No. 10/330,881, filed December 23, 2002. Such prior disclosure is sufficient for the above-identified application as far as copies of the references are concerned. 37 C.F.R. § 1.98(d) and MPEP § 609(2).

Citation of these references is respectfully requested.

Respectfully submitted,

Dated: 10-16-03

By: _____
Mark S. Matkin
Reg. No. 32,268

Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTORNEY DOCKET NO. MI22-2416	PRIORITY SERIAL NO. 10/330,881
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		APPLICANT: Trung Tri Doan et al.	
		PRIORITY FILING DATE December 23, 2002	PRIORITY GROUP ART UNIT 2813

U.S. PATENT DOCUMENTS

*Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	3,990,927	11/1976	Montier			
	AB	4,474,975	10/1984	Clemons et al.			
	AC	5,156,881	10/1992	Okano et al.			
	AD	5,182,221	01/1993	Sato			
	AE	5,410,176	04/1995	Liou et al.			
	AF	5,470,798	11/1995	Ouellet			
	AG	5,719,085	02/1998	Moon et al.			
	AH	5,741,740	04/1998	Jang et al.			
	AI	5,776,557	07/1998	Okano et al.			

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AJ	02277253A	11/1990	Japan (Hayashide et al.)				
	AK	146224	01/1996	Japan				
	AL							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AM		Beekmann et al., *Sub-micron Gap Fill and In-Situ Planarisation using Flowfill™ Technology*, Electrotech 1-7
			ULSI Conference, Portland, OR (October 1995).
	AN		Horie et al., *Kinetics and Mechanism of the Reactions of $O(^3P)$ with SiH_4, CH_3SiH_3, $(CH_3)_2SiH_2$, and*
			$(CH_3)_3SiH$, 95 J. PHYS. CHEM 4393-4400 (1991).
	AO		Joshi et al., *Plasma Deposited Organosilicon Hydride Network Polymers as Versatile Resists for Entirely Dry*
			Mid-Deep UV Photolithography, 1925 SPIE 709-720 (January 1993).

EXAMINER	DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	AA	5,786,039	07/1998	Brouquet			
	AB	5,801,083	09/1998	Yu et al.			
	AC	5,863,827	01/1999	Joyner			
	AD	5,883,006	03/1999	Iba			
	AE	5,888,880	03/1999	Gardner et al.			
	AF	5,895,253	04/1999	Akram			
	AG	5,904,540	05/1999	Sheng et al.			
	AH	5,930,645	07/1999	Lyons et al.			
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	AK							
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	AM		Kiermasz et al., *Planarisation for Sub-Micron Devices Utilising a New Chemistry*, Electrotech 1-2, DUMIC
			Conference, California (February 1995).
	AN		Kojima et al., *Planarization Process Using a Multi-Coating of Spin-on-Glass*, V-MIC Conference, pp. 390-396
			(June 13-14, 1988).
	AO		Matsuura et al., *A Highly Reliable Self-planarizing Low-k Intermetal Dielectric for Sub-quarter Micron*
			Interconnects, 97 IEEE 785-788 (July 1997).

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	AA	5,950,094	09/1999	Lin et al.			
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	AD	5,998,280	12/1999	Bergemont et al.			
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	AF	6,051,477	04/2000	Nam			
	AG	6,156,674	12/2000	Li et al.			
	AH	6,300,219 B1	10/2001	Doan et al.			
	AI						

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							Yes	No
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	AL							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

	AM		Matsuura et al., *Novel Self-planarizing CVD Oxide for Interlayer Dielectric Applications*, 94 IEEE 117-120 (1994).
	AN		McClatchie et al. *Low Dielectric Constant Flowfill™ Technology for IMD Applications*, 7 pages (pre-August 1999).
	AO		Withnall et al., *Matrix Reactions of Methylsilanes and Oxygen Atoms*, 92 J. PHYS. CHEM. 594-602 (1988).

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